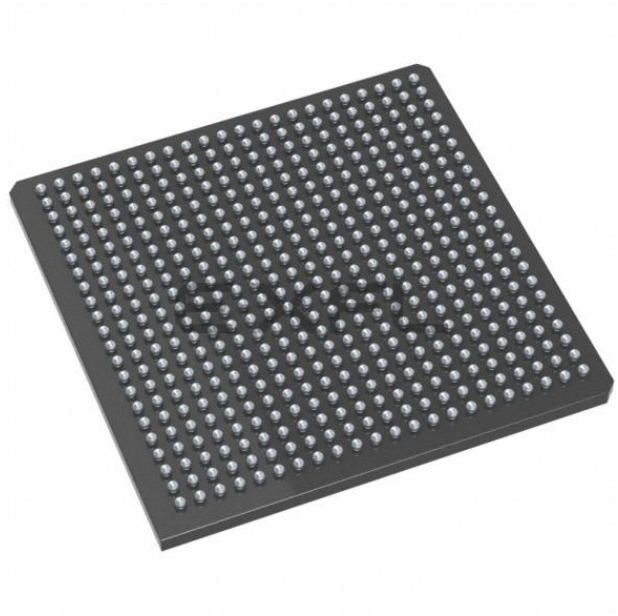

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What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 154K+ Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	484-BFBGA, FCBGA
Supplier Device Package	484-FCBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu3cg-2sbva484i

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
Processor System					
$V_{CC\_PSINTFP}$(3)	PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS full-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS full-power domain supply voltage.	0.873	0.900	0.927	V
$V_{CC\_PSINTLP}$	PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS low-power domain supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS low-power domain supply voltage.	0.873	0.900	0.927	V
V_{CC_PSAUX}	PS auxiliary supply voltage.	1.710	1.800	1.890	V
$V_{CC\_PSINTFP\_DDR}$(3)	PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PS DDR controller and PHY supply voltage.	0.808	0.850	0.892	V
	For -3E devices: PS DDR controller and PHY supply voltage.	0.873	0.900	0.927	V
V_{CC_PSADC}	PS SYSMON ADC supply voltage relative to GND_PSADC.	1.710	1.800	1.890	V
V_{CC_PSPLL}	PS PLL supply voltage.	1.164	1.200	1.236	V
$V_{PS\_MGTRAVCC}$	PS-GTR supply voltage.	0.825	0.850	0.875	V
$V_{PS\_MGTRAVTT}$	PS-GTR termination voltage.	1.746	1.800	1.854	V
V_{CCO_PSDDR}(4)	PS DDR I/O supply voltage.	1.06	–	1.575	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	1.710	1.800	1.890	V
V_{CCO_PSIO}(5)	PS I/O supply.	1.710	–	3.465	V
V_{PSIN}	PS I/O input voltage.	–0.200	–	V_{CCO_PSIO} + 0.200	V
	PS DDR I/O input voltage.	–0.200	–	V_{CCO_PSDDR} + 0.200	
V_{CC_PSBATT}(6)	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	1.200	–	1.500	V
Programmable Logic					
V_{CCINT}	PL internal supply voltage.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: PL internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(7)	PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -1LI and -2LE (V_{CCINT} = 0.72V) devices: PL internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: PL internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
I_{CC_PSBATT}(4)(5)	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC enabled.	–	–	3650	nA
	Battery supply current at V_{CC_PSBATT} = 1.50V, RTC disabled.	–	–	650	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC enabled.	–	–	3150	nA
	Battery supply current at V_{CC_PSBATT} = 1.20V, RTC disabled.	–	–	150	nA
I_{PSFS}(6)	PS V_{CC_PSAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in HP I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(7)	40	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(7)	48	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(7)	60	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(7)	120	+10%(7)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(7)	240	+10%(7)	Ω
Uncalibrated programmable on-die termination in HP I/Os banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Uncalibrated programmable on-die termination in HD I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 where ODT = RTT_48.	–50%	48	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

Quiescent Supply Current

Table 9: **Typical Quiescent Supply Current(1)(2)(3)(4)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XCZU2	N/A	393	393	344	344	mA
		XCZU3	N/A	393	393	344	344	mA
		XCZU4	719	684	684	601	601	mA
		XCZU5	719	684	684	601	601	mA
		XCZU6	1629	1549	1549	1358	1358	mA
		XCZU7	1263	1201	1201	1055	1055	mA
		XCZU9	1629	1549	1549	1358	1358	mA
		XCZU11	1786	1699	1699	1491	1491	mA
		XCZU15	1987	1890	1890	1660	1660	mA
		XCZU17	2728	2594	2594	2275	2275	mA
		XCZU19	2728	2594	2594	2275	2275	mA
I_{CCINT_IOQ}	Quiescent V_{CCINT_IO} supply current.	XCZU2	N/A	44	44	44	44	mA
		XCZU3	N/A	44	44	44	44	mA
		XCZU4	61	59	59	59	59	mA
		XCZU5	61	59	59	59	59	mA
		XCZU6	61	59	59	59	59	mA
		XCZU7	120	115	115	115	115	mA
		XCZU9	61	59	59	59	59	mA
		XCZU11	120	115	115	115	115	mA
		XCZU15	61	59	59	59	59	mA
		XCZU17	164	158	158	158	158	mA
		XCZU19	164	158	158	158	158	mA
I_{CCOQ}	Quiescent V_{CCO} supply current.	All devices	1	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XCZU2	N/A	55	55	55	55	mA
		XCZU3	N/A	55	55	55	55	mA
		XCZU4	90	90	90	90	90	mA
		XCZU5	90	90	90	90	90	mA
		XCZU6	227	227	227	227	227	mA
		XCZU7	174	174	174	174	174	mA
		XCZU9	227	227	227	227	227	mA
		XCZU11	255	255	255	255	255	mA
		XCZU15	266	266	266	266	266	mA
		XCZU17	396	396	396	396	396	mA
		XCZU19	396	396	396	396	396	mA

Table 15: **SelectIO DC Input and Output Levels for HP I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	5.8	–5.8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	4.1	–4.1
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	6.2	–6.2
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.0	–8.0
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	9.0	–9.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	10.0	–10.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	7.0	–7.0
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in HP I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 16: **DC Input Levels for Single-ended POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{IL}		V_{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300
POD12	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 26: **Speed Grade Designations by Device *(Cont'd)***

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	**Preliminary**	**Production**
XCZU5EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU5EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU6CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU6EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU7CG	-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EG	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU7EV	-3E (V_{CCINT} = 0.90V), -2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V), -1LI (V_{CCINT} = 0.72V)		
XCZU9CG	-2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCZU9EG	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V) -1LI (V_{CCINT} = 0.85V) -1LI (V_{CCINT} = 0.72V)		-2E (V_{CCINT} = 0.85V) -2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)

PS Switching Characteristics

PS Clocks

Table 34: **PS Reference Clock Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
$T_{RMSJPSCLK}$	PS_REF_CLK input RMS clock jitter.	–	–	3	ps
$T_{PJPSCLK}$	PS_REF_CLK input period jitter (peak-to-peak). Number of clock cycles = 10,000	–	–	50	ps
$T_{DCPSCLK}$	PS_REF_CLK duty cycle.	45	–	55	%
$T_{RFPSCLK}$	PS_REF_CLK rise time (20%–80%) and fall time (80%–20%).	–	–	2.22	ns
F_{PSCLK}	PS_REF_CLK frequency.	27	–	60	MHz

Notes:

1. The values in this table are applicable to alternative PS reference clock inputs ALT_REF_CLK, AUX_REF_CLK, and VIDEO_CLK.

Table 35: **PS RTC Crystal Requirements**(1)

Symbol	Description	Min	Typ	Max	Units
F_{XTAL}	Parallel resonance crystal frequency.	–	32.8	–	KHz
T_{FTXTAL}	Frequency tolerance.	–20	–	20	ppm
C_{XTAL}	Load capacitance for crystal parallel resonance.	–	12.5	–	pF
R_{ESR}	Crystal ESR (16.8 and 19.2 MHz).	–	70	–	KΩ
C_{SHUNT}	Crystal shunt capacitance.	–	1.4	–	pF

Notes:

1. Required board components: Feedback resistor = 4.7 MΩ, PCB and pad capacitance = 1.5 pF, C_1 and C_2 capacitance = 21 pF.

Table 36: **PS PLL Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{LOCKPSPLL}$	PLL maximum lock time.	100	100	100	µs
$F_{PSPLLMAX}$	PLL maximum output frequency.	1600	1600	1600	MHz
$F_{PSPLLMIN}$	PLL minimum output frequency.	750	750	750	MHz
$F_{PSPLLVCOMAX}$	PLL maximum VCO frequency.	3000	3000	3000	MHz
$F_{PSPLLVCOMIN}$	PLL minimum VCO frequency.	1500	1500	1500	MHz

Table 61: **PS-GTR Transceiver Reference Clock Oscillator Selection Phase Noise Mask**

Symbol	Description	Offset Frequency	Min	Typ	Max	Units
$PLL_{REFCLKMASK}$	PLL reference clock select phase noise mask at REFCLK frequency = 25 MHz.	100	–	–	–102	dBc/Hz
		1 KHz	–	–	–124	
		10 KHz	–	–	–132	
		100 KHz	–	–	–139	
		1 MHz	–	–	–152	
		10 MHz	–	–	–154	
	PLL reference clock select phase noise mask at REFCLK frequency = 50 MHz.	100	–	–	–96	dBc/Hz
		1 KHz	–	–	–118	
		10 KHz	–	–	–126	
		100 KHz	–	–	–133	
		1 MHz	–	–	–146	
		10 MHz	–	–	–148	
	PLL reference clock select phase noise mask at REFCLK frequency = 100 MHz.	100	–	–	–90	dBc/Hz
		1 KHz	–	–	–112	
		10 KHz	–	–	–120	
		100 KHz	–	–	–127	
		1 MHz	–	–	–140	
		10 MHz	–	–	–142	
	PLL reference clock select phase noise mask at REFCLK frequency = 125 MHz.	100	–	–	–88	dBc/Hz
		1 KHz	–	–	–110	
		10 KHz	–	–	–118	
		100 KHz	–	–	–125	
		1 MHz	–	–	–138	
		10 MHz	–	–	–140	
	PLL reference clock select phase noise mask at REFCLK frequency = 150 MHz.	100	–	–	–86	dBc/Hz
		1 KHz	–	–	–108	
		10 KHz	–	–	–116	
		100 KHz	–	–	–123	
		1 MHz	–	–	–136	
		10 MHz	–	–	–138	

Notes:

1. For reference clock frequencies not in this table, use the phase noise mask for the nearest reference clock frequency.

Table 62: **PS-GTR Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTRTX}	Serial data rate range.		1.25	–	6.0	Gb/s
T_{RTX}	TX rise time.	20%–80%	–	65	–	ps
T_{FTX}	TX fall time.	80%–20%	–	65	–	ps

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

Table 75: **IOB High Density (HD) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
LVCMOS33_S_8	1.154	1.154	1.213	1.154	1.213	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
LVDS_25	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVPECL	1.003	1.003	1.116	1.003	1.116	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
LVTTL_F_12	1.164	1.164	1.223	1.164	1.223	2.415	2.415	2.651	2.415	2.651	1.754	1.754	1.915	1.754	1.915	ns
LVTTL_F_16	1.164	1.164	1.223	1.164	1.223	2.464	2.464	2.732	2.464	2.732	1.750	1.750	1.986	1.750	1.986	ns
LVTTL_F_4	1.164	1.164	1.223	1.164	1.223	2.541	2.541	2.765	2.541	2.765	1.932	1.932	2.135	1.932	2.135	ns
LVTTL_F_8	1.164	1.164	1.223	1.164	1.223	2.582	2.582	2.787	2.582	2.787	1.910	1.910	2.063	1.910	2.063	ns
LVTTL_S_12	1.164	1.164	1.223	1.164	1.223	2.731	2.731	3.075	2.731	3.075	2.072	2.072	2.343	2.072	2.343	ns
LVTTL_S_16	1.164	1.164	1.223	1.164	1.223	2.714	2.714	3.024	2.714	3.024	2.028	2.028	2.232	2.028	2.232	ns
LVTTL_S_4	1.164	1.164	1.223	1.164	1.223	2.999	2.999	3.340	2.999	3.340	2.320	2.320	2.610	2.320	2.610	ns
LVTTL_S_8	1.164	1.164	1.223	1.164	1.223	2.929	2.929	3.260	2.929	3.260	2.260	2.260	2.532	2.260	2.532	ns
SLVS_400_25	1.020	1.020	1.136	1.020	1.136	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_F	0.780	0.780	0.867	0.780	0.867	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
SSTL12_S	0.780	0.780	0.867	0.780	0.867	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
SSTL135_F	0.798	0.798	0.881	0.798	0.881	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
SSTL135_II_F	0.798	0.798	0.881	0.798	0.881	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
SSTL135_II_S	0.798	0.798	0.881	0.798	0.881	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
SSTL135_S	0.798	0.798	0.881	0.798	0.881	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
SSTL15_F	0.838	0.838	0.880	0.838	0.880	1.612	1.612	1.754	1.612	1.754	1.357	1.357	1.464	1.357	1.464	ns
SSTL15_II_F	0.838	0.838	0.880	0.838	0.880	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
SSTL15_II_S	0.838	0.838	0.880	0.838	0.880	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
SSTL15_S	0.838	0.838	0.880	0.838	0.880	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
SSTL18_II_F	0.947	0.947	1.021	0.947	1.021	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
SSTL18_II_S	0.947	0.947	1.021	0.947	1.021	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
SSTL18_I_F	0.947	0.947	1.021	0.947	1.021	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
SSTL18_I_S	0.947	0.947	1.021	0.947	1.021	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
SUB_LVDS	1.002	1.002	1.036	1.002	1.036	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns

Block RAM and FIFO Switching Characteristics

Table 80: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
Maximum Frequency							
$F_{MAX\_WF\_NC}$	Block RAM (WRITE_FIRST and NO_CHANGE modes).	825	738	645	585	516	MHz
F_{MAX_RF}	Block RAM (READ_FIRST mode).	718	637	575	510	460	MHz
F_{MAX_FIFO}	FIFO in all modes without ECC.	825	738	645	585	516	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration without PIPELINE.	718	637	575	510	460	MHz
	Block RAM and FIFO in ECC configuration with PIPELINE and Block RAM in WRITE_FIRST or NO_CHANGE mode.	825	738	645	585	516	MHz
T_{PW}[(1)]	Minimum pulse width.	495	542	543	577	578	ps
Block RAM and FIFO Clock-to-Out Delays							
T_{RCKO_DO}	Clock CLK to DOUT output (without output register).	0.91	1.02	1.11	1.46	1.53	ns, Max
$T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (with output register).	0.27	0.29	0.30	0.42	0.44	ns, Max

Notes:

1. The MMCM and PLL DUTY_CYCLE attribute should be set to 50% to meet the pulse-width requirements at the higher frequencies.

Table 85: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
MMCM_F_{DPRCLK_MAX}	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.

Table 88: **Global Clock Input to Output Delay Without MMCM (Far Clock Region)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF_FAR}	Global clock input and output flip-flop *without* MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: **Global Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
$T_{ICKOFMMCMCC}$	Global clock input and output flip-flop *with* MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
		XCZU19	2.44	2.44	2.66	3.19	3.17	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 103: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHTX}	Serial data rate range		0.500	–	F_{GTHMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.0}$	Total jitter(3)(4)	4.0 Gb/s	–	–	0.32	UI
$D_{J4.0}$	Deterministic jitter(3)(4)		–	–	0.16	UI
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI

Table 104: **GTH Transceiver Receiver Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:
1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTH Transceiver Electrical Compliance

The *UltraScale Architecture GTH Transceiver User Guide* (UG576) contains recommended use modes that ensure compliance for the protocols listed in Table 105. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

GTY Transceiver Specifications

The *UltraScale Architecture and Product Overview* (DS890) lists the Zynq UltraScale+ MPSoCs that include the GTY transceivers.

GTY Transceiver DC Input and Output Levels

Table 106 and Table 107 summarize the DC specifications of the GTY transceivers in Zynq UltraScale+ MPSoCs. Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further details.

Table 106: **GTY Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV_{PPIN}	Differential peak-to-peak input voltage (external AC coupled)	>10.3125 Gb/s	150	–	1250	mV
		6.6 Gb/s to 10.3125 Gb/s	150	–	1250	mV
		≤ 6.6 Gb/s	150	–	2000	mV
V_{IN}	Single-ended input voltage. Voltage measured at the pin referenced to GND.	DC coupled $V_{MGTAVTT}$ = 1.2V	–400	–	$V_{MGTAVTT}$	mV
V_{CMIN}	Common mode input voltage	DC coupled $V_{MGTAVTT}$ = 1.2V	–	2/3 $V_{MGTAVTT}$	–	mV
D_{VPPOUT}	Differential peak-to-peak output voltage(1)	Transmitter output swing is set to 11111	800	–	–	mV
$V_{CMOUTDC}$	Common mode output voltage: DC coupled (equation based)	When remote RX is terminated to GND	$V_{MGTAVTT}/2 - D_{VPPOUT}/4$			mV
		When remote RX termination is floating	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
		When remote RX is terminated to V_{RX_TERM}(2)	$V_{MGTAVTT} - \frac{D_{VPPOUT}}{4} - \left(\frac{V_{MGTAVTT} - V_{RX\_TERM}}{2}\right)$			mV
$V_{CMOUTAC}$	Common mode output voltage: AC coupled	Equation based	$V_{MGTAVTT} - D_{VPPOUT}/2$			mV
R_{IN}	Differential input resistance		–	100	–	Ω
R_{OUT}	Differential output resistance		–	100	–	Ω
T_{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	–	10	ps
C_{EXT}	Recommended external AC coupling capacitor(3)		–	100	–	nF

Notes:

1. The output swing and pre-emphasis levels are programmable using the GTY transceiver attributes discussed in the *UltraScale Architecture GTY Transceiver User Guide* (UG578) and can result in values lower than reported in this table.
2. V_{RX_TERM} is the remote RX termination voltage.
3. Other values can be used as appropriate to conform to specific protocols and standards.

Table 115: **GTY Transceiver Transmitter Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J2.5}$	Total jitter(3)(4)	2.5 Gb/s(6)	–	–	0.20	UI
$D_{J2.5}$	Deterministic jitter(3)(4)		–	–	0.10	UI
$T_{J1.25}$	Total jitter(3)(4)	1.25 Gb/s(7)	–	–	0.15	UI
$D_{J1.25}$	Deterministic jitter(3)(4)		–	–	0.06	UI
T_{J500}	Total jitter(3)(4)	500 Mb/s(8)	–	–	0.10	UI
D_{J500}	Deterministic jitter(3)(4)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTY Quad) at maximum line rate.
2. Using QPLL_FBDIV = 40, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. Using CPLL_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
4. All jitter values are based on a bit-error ratio of 10^{-12}.
5. CPLL frequency at 3.2 GHz and TXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. CPLL frequency at 2.5 GHz and TXOUT_DIV = 4.
8. CPLL frequency at 2.0 GHz and TXOUT_DIV = 8.

Table 116: **GTY Transceiver Receiver Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTYRX}	Serial data rate		0.500	–	F_{GTYMAX}	Gb/s
R_{XSST}	Receiver spread-spectrum tracking(1)	Modulated at 33 kHz	–5000	–	0	ppm
R_{XRL}	Run length (CID)		–	–	256	UI
$R_{XPPMTOL}$	Data/REFCLK PPM offset tolerance	Bit rates ≤ 6.6 Gb/s	–1250	–	1250	ppm
		Bit rates > 6.6 Gb/s and ≤ 8.0 Gb/s	–700	–	700	ppm
		Bit rates > 8.0 Gb/s	–200	–	200	ppm
SJ Jitter Tolerance(2)						
$J_{T\_SJ32.75}$	Sinusoidal jitter (QPLL)(3)	32.75 Gb/s	0.25	–	–	UI
$J_{T\_SJ28.21}$	Sinusoidal jitter (QPLL)(3)	28.21 Gb/s	0.30	–	–	UI
$J_{T\_SJ16.375}$	Sinusoidal jitter (QPLL)(3)	16.375 Gb/s	0.30	–	–	UI
$J_{T\_SJ15.0}$	Sinusoidal jitter (QPLL)(3)	15.0 Gb/s	0.30	–	–	UI
$J_{T\_SJ14.1}$	Sinusoidal jitter (QPLL)(3)	14.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ13.1}$	Sinusoidal jitter (QPLL)(3)	13.1 Gb/s	0.30	–	–	UI
$J_{T\_SJ12.5}$	Sinusoidal jitter (QPLL)(3)	12.5 Gb/s	0.30	–	–	UI
$J_{T\_SJ11.3}$	Sinusoidal jitter (QPLL)(3)	11.3 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_QPLL}$	Sinusoidal jitter (QPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ10.32\_CPLL}$	Sinusoidal jitter (CPLL)(3)	10.32 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_QPLL}$	Sinusoidal jitter (QPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ9.953\_CPLL}$	Sinusoidal jitter (CPLL)(3)	9.953 Gb/s	0.30	–	–	UI
$J_{T\_SJ8.0}$	Sinusoidal jitter (CPLL)(3)	8.0 Gb/s	0.42	–	–	UI
$J_{T\_SJ6.6}$	Sinusoidal jitter (CPLL)(3)	6.6 Gb/s	0.44	–	–	UI
$J_{T\_SJ5.0}$	Sinusoidal jitter (CPLL)(3)	5.0 Gb/s	0.44	–	–	UI
$J_{T\_SJ4.25}$	Sinusoidal jitter (CPLL)(3)	4.25 Gb/s	0.44	–	–	UI
$J_{T\_SJ3.2}$	Sinusoidal jitter (CPLL)(3)	3.2 Gb/s(4)	0.45	–	–	UI
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTY Transceiver Electrical Compliance

The *UltraScale Architecture GTY Transceiver User Guide* (UG578) contains recommended use modes that ensure compliance for the protocols listed in Table 117. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 117: **GTY Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-4	IEEE 802.3-2012	25.78125	Compliant
28 Gb/s backplane	CEI-25G-LR	25–28.05	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11GSR, OIF-CEI-28G-MR	4.25–25.78125	Compliant
100GBASE-KR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
100GBASE-CR4	IEEE 802.3bj-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
50GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-KR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
25GBASE-CR4	IEEE 802.3by-2014, CEI-25G-LR	25.78125	Compliant(1)
OTU4 (OTL4.4) CFP2	OIF-CEI-28G-VSR	27.952493–32.75	Compliant
OTU4 (OTL4.4) CFP	OIF-CEI-11G-MR	11.18–13.1	Compliant
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(2)	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
QSGMII	QSGMII v1.2 (Cisco System, ENG-46158)	5	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(3)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(3)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys bandwidth engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant

Date	Version	Description of Revisions
02/10/2017	1.2	Updated some of the maximum voltages in the Processor System (PS) section and other specifications in the Programmable Logic (PL) and GTH or GTY Transceiver sections of Table 1. Updated Table 2, Table 4, Table 6, Table 7, and Table 9. Revised the Power Supply Sequencing section including Table 10. Added PS and VCU ramp times to Table 11. Revised V_{ODIFF} in Table 24. Updated Table 25. Added Note 1 to Table 26. Table 30 replaces the previous three PS memory performance tables. Added values to Table 34, Table 37, and Table 38. Deleted the waveforms in the PS Switching Characteristics section (Figures 1-16 and Figures 25-26). Revised values in the *PS NAND Memory Controller Interface* section. Added and updated data in Table 40. Added Note 3 to Table 41. Added Note 3 to Table 42. Added Note 1 to Table 45. Updated Table 48 and removed Note 3. Added data to Table 56. Updated Table 60. Added Table 61. Updated Table 63. Revised Table 69. Added data to Table 70. Added Note 2 to Table 71. Updated Table 74 and added Note 4. Updated V_L and V_H values in Table 78. Added T_{MINPER_CLK}, revised F_{REFCLK}, and Note 1 to Table 82. Added MMCM_F_{DPRCLK_MAX} to Table 85 and PLL_F_{DPRCLK_MAX} to Table 86. Added data to Table 94, Table 96, Table 98, Table 101, and updated the note references in Table 102. Updated Table 103 and added Note 8. Updated Table 104 and added Note 7. Added more protocols, Note 1 and Note 2 to Table 105. Removed the *GTH Transceiver Protocol Jitter Characteristics* section because it is covered in Table 105. Added Note 1 to Table 109. Added data to Table 106, Table 108, Table 110, Table 113. Added Note 2 to Table 112. Added note references in Table 114. Updated Table 115 and added Note 8. Updated Table 116 and added Note 7. Added more protocols and Note 3 to Table 117. Removed the *GTY Transceiver Protocol Jitter Characteristics* section because it is covered in Table 117. Revised Table 124. Added T_{POR} and updated F_{ICAPCK} in Table 127. Updated the Automotive Applications Disclaimer.
06/20/2016	1.1	Updated the Summary description. In Table 1, revised V_{IN} for HP I/O banks and added clarifications to some descriptions and symbols. Added I_{RPU}, I_{RPD}, and Note 4 to Table 2 and updated $V_{PS\_MGTRAVCC}$, the PL System Monitor section, and Note 3 and Note 5. Updated Note 5 in Table 4. Updated the PS Power-On/Off Power Supply Sequencing section including all the voltage supply names. Added MIPI_DPHY_DCI to Table 14, Table 15, and Table 17. Updated Table 23, including removing the V_{CCO} specification and adding Note 1. Added Note 1 to Table 24. Updated Table 25 speed specifications for Vivado Design Suite 2016.1. Added values to Table 28. Updated the -2 value in Table 29. Added $F_{DPLIVEVIDEO}$ and updated $F_{FCIDMACLK}$ in Table 33. Added VCO frequencies to Table 36. Added the T_{PSPOR} minimum to Table 37 and updated Note 1. Added Table 38. Added value delineation over V_{CCINT} operating voltages in Table 39. Revised values for F_{TCK} and T_{TAPTCK}/T_{TCKTAP} in Table 40 and added value delineation over V_{CCINT} operating voltages. Updated the *PS NAND Memory Controller Interface* section. Revised some units and Note 1 in Table 41 and Table 42. Removed Figure 6: Quad-SPI Interface (Feedback Clock Disabled) Timing. Updated Note 1 of Table 43. Added $F_{TSI\_REF\_CLK}$ to Table 44 and updated Note 1. In Table 45, revised $T_{DCSDHSCLK1}$, $T_{DCSDHSCLK2}$, and $T_{DCSDHSCLK3}$ and Note 1. In Table 46, revised Note 1. In Table 47, revised Note 1. Revised Table 48, including Note 1, and added Note 2 and Note 3. In Table 49, Table 50, Table 51, and Table 53, revised Note 1. Updated Table 71. Replaced Table 74. Updated Table 75 and Table 76. Updated Table 78 and Table 79. In Table 80, added the Block RAM and FIFO Clock-to-Out Delays section. Updated the R_{IN} and C_{EXT} values in Table 57 and Table 95. Updated the -2 (0.72V) and -1 (0.72V) values and added Note 1 to Table 97. Added Table 100 and Table 112. Added Note 2 to Table 106. Revised data in Table 109. Revised Table 114. Revised data and added notes in the Integrated Interface Block for Interlaken section and Table 121. Moved Table 123. Revised INL in Table 124. Added notes to Table 125 and Table 126. In the *eFUSE and Programming Conditions* table, updated the I_{PSFS} description.
11/24/2015	1.0	Initial Xilinx release.